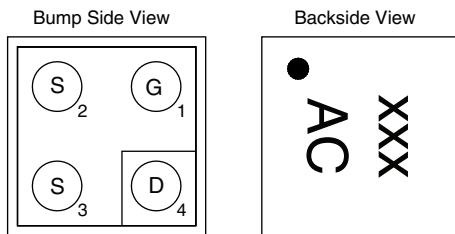




P-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 8	0.068 at V _{GS} = - 4.5 V	- 3.1	6.7 nC
	0.088 at V _{GS} = - 2.5 V	- 2.7	
	0.155 at V _{GS} = - 1.5 V	- 2.1	
	0.290 at V _{GS} = - 1.2 V	- 0.5	

MICRO FOOT



Device Marking: xxx = Date/Lot Traceability Code
AC

Ordering Information: Si8805EDB-T2-E1 (Lead (Pb)-free and Halogen-free)

FEATURES

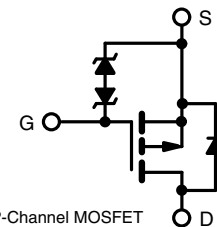
- TrenchFET[®] Power MOSFET
- Ultra Small 0.8 mm x 0.8 mm Outline
- Ultra Thin 0.357 mm Height
- Typical ESD Protection 1500 V HBM
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable Devices such as Cell Phones, Smart Phones, Tablet PCs and Media Players
 - Load Switch for Low Voltage Gate Drive
 - Load Switch for 1.2 V Power Line



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 8	V	
Gate-Source Voltage	V _{GS}	± 5		
Continuous Drain Current (T _J = 150 °C)	I _D	T _A = 25 °C	- 3.1 ^a	A
		T _A = 70 °C	- 2.5 ^a	
		T _A = 25 °C	- 2.2 ^b	
		T _A = 70 °C	- 1.8 ^b	
Pulsed Drain Current	I _{DM}	- 15		
Continuous Source-Drain Diode Current	I _S	T _A = 25 °C	- 0.7 ^a	
		T _A = 25 °C	- 0.4 ^b	
Maximum Power Dissipation	P _D	T _A = 25 °C	0.9 ^a	W
		T _A = 70 °C	0.6 ^a	
		T _A = 25 °C	0.5 ^b	
		T _A = 70 °C	0.3 ^b	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^c		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, d}	R _{thJA}	105	135	°C/W	
Maximum Junction-to-Ambient ^{b, e}		200	260		

Notes:

- Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, t = 5 s.
- Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.
- Maximum under steady state conditions is 185 °C/W.
- Maximum under steady state conditions is 330 °C/W.

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	- 8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 4		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 0.35		- 0.7	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 5\text{ V}$			± 1.5	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	
		$V_{DS} = -8\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -4\text{ V}$, $V_{GS} = -4.5\text{ V}$	- 5			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -1.5\text{ A}$		0.056	0.068	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -1.5\text{ A}$		0.070	0.088	
		$V_{GS} = -1.5\text{ V}$, $I_D = -0.5\text{ A}$		0.115	0.155	
		$V_{GS} = -1.2\text{ V}$, $I_D = -0.3\text{ A}$		0.190	0.290	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -4\text{ V}$, $I_D = -1.5\text{ A}$		8		S
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -1.5\text{ A}$		6.7	10	nC
Gate-Source Charge	Q_{gs}			0.7		
Gate-Drain Charge	Q_{gd}			1.8		
Gate Resistance	R_g	$f = 1\text{ MHz}$		10		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}$, $R_L = 2.7\text{ }\Omega$ $I_D = -1.5\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$		13	25	ns
Rise Time	t_r			13	25	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	t_f			17	35	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 0.7	A
Pulse Diode Forward Current	I_{SM}				- 15	
Body Diode Voltage	V_{SD}	$I_S = -1.5\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$		35	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			15	30	nC
Reverse Recovery Fall Time	t_a			15		ns
Reverse Recovery Rise Time	t_b			20		

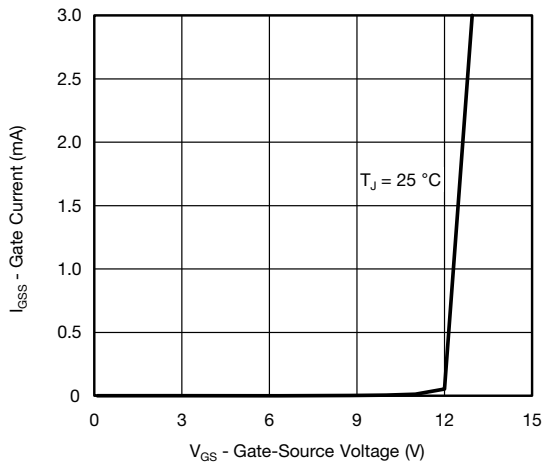
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing.

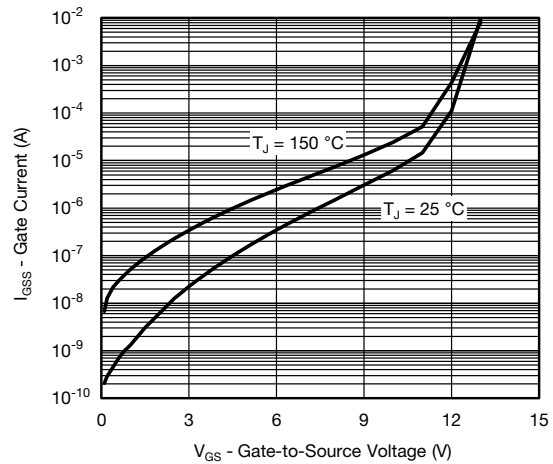
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



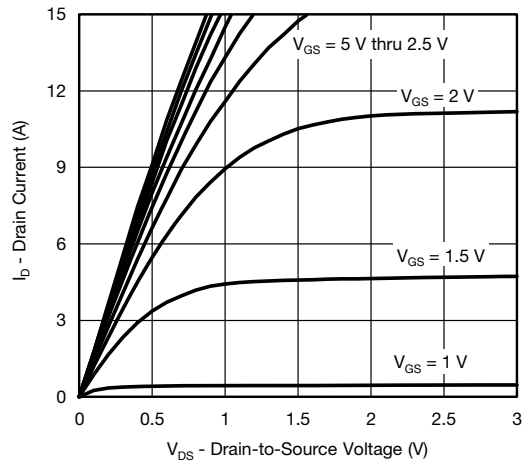
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



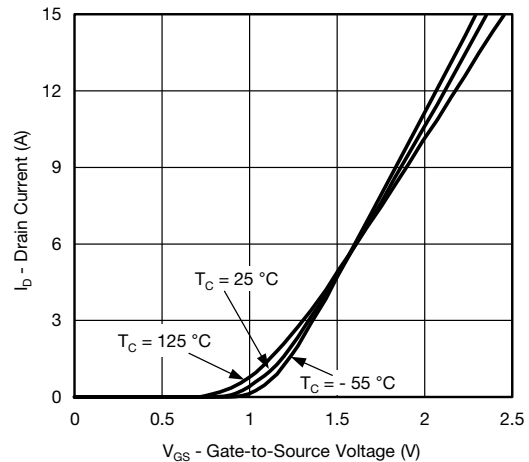
Gate Current vs. Gate-Source Voltage



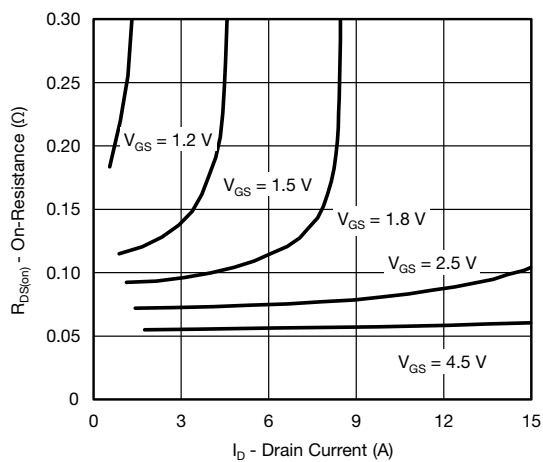
Gate Current vs. Gate-Source Voltage



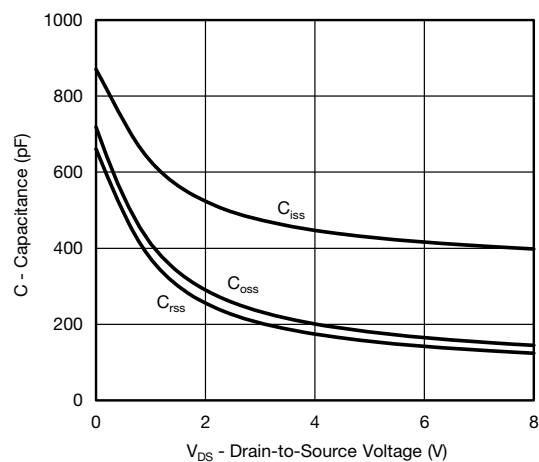
Output Characteristics



Transfer Characteristics

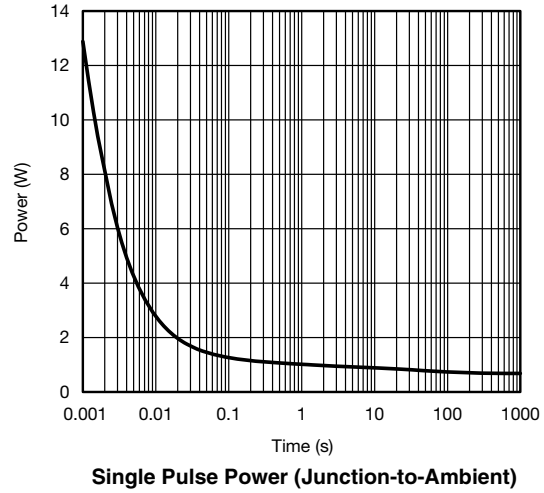
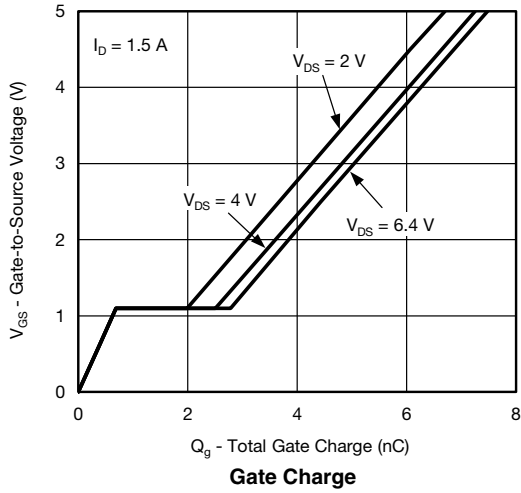


On-Resistance vs. Drain Current

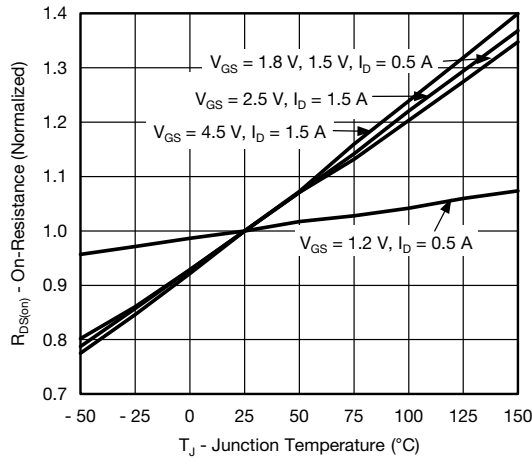


Capacitance

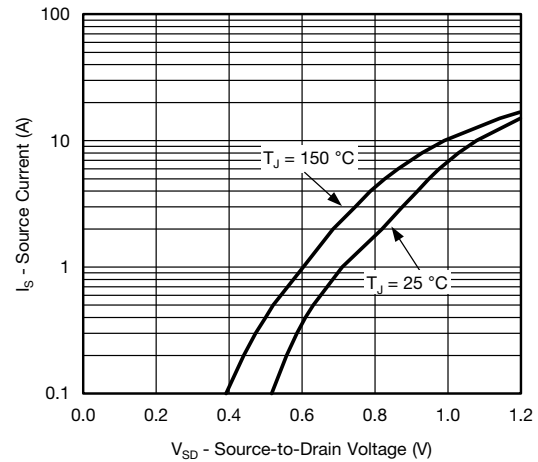
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



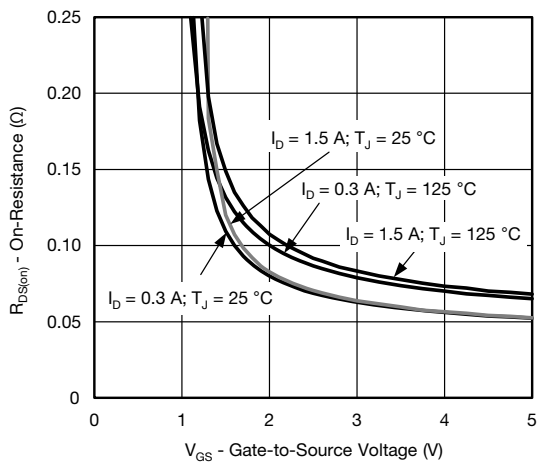
Single Pulse Power (Junction-to-Ambient)



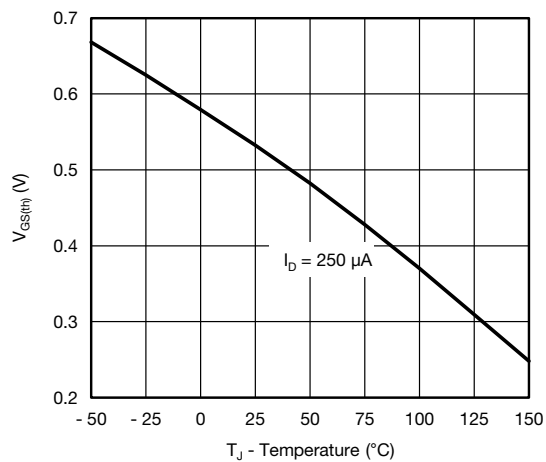
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



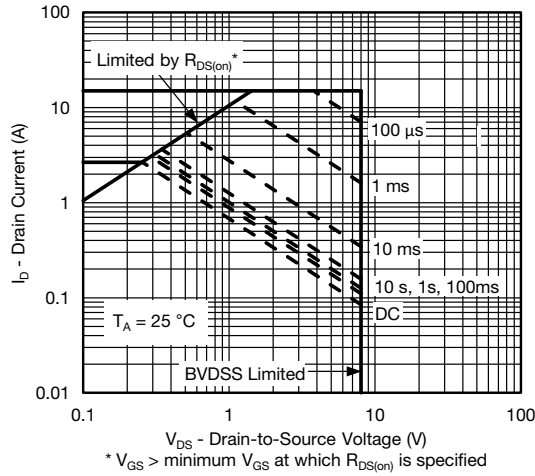
On-Resistance vs. Gate-to-Source Voltage



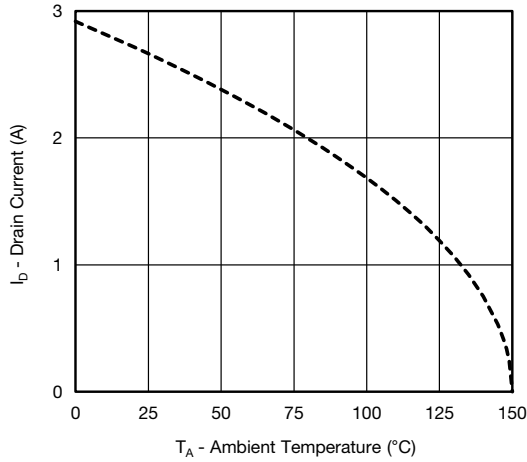
Threshold Voltage



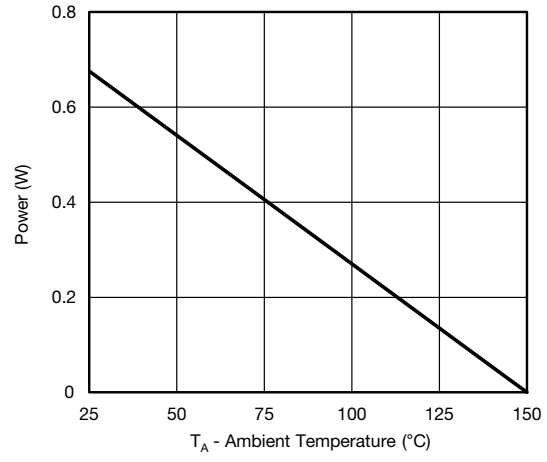
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient



Current Derating*

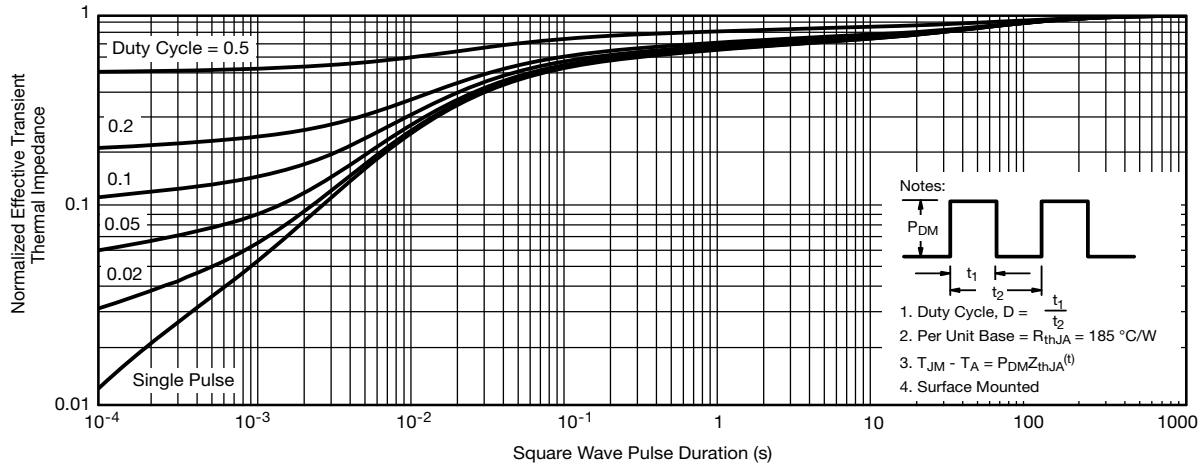


Power Derating

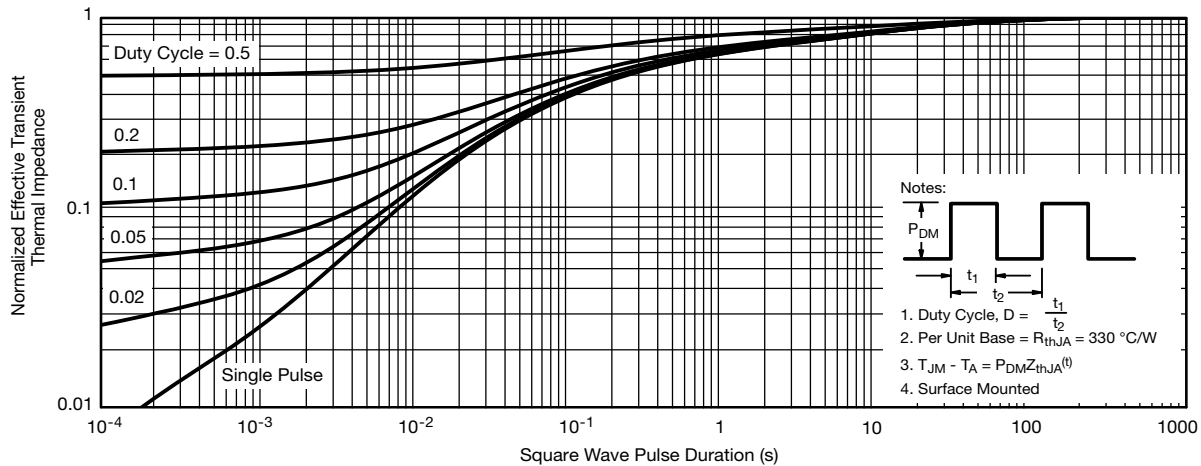
Note:
When mounted on 1" x 1" FR4 with full copper.

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



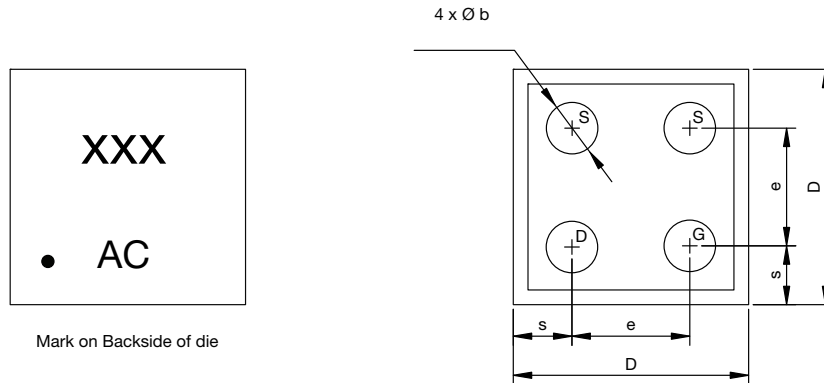
Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with maximum copper)



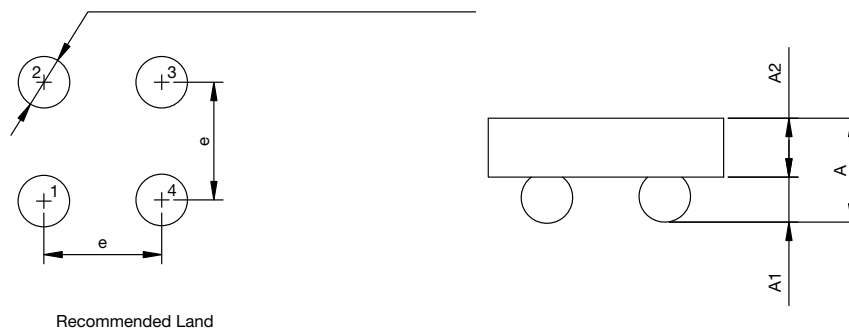
Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with minimum copper)

PACKAGE OUTLINE

MICRO FOOT 0.8 mm x 0.8 mm: 4-BUMP (2 x 2, 0.4 mm PITCH)



4 x Ø 0.205 to 0.225 Note 4
Solder Mask ~ Ø 0.215



Notes (unless otherwise specified):

1. All dimensions are in millimeters.
2. Four (4) solder bumps are lead (Pb)-free 95.5Sn/3.5Ag/0.7Cu with diameter Ø 0.165 mm to Ø 0.185 mm.
3. Backside surface is coated with a Ti/Ni/Ag layer.
4. Non-solder mask defined copper landing pad.
5. • is location of pin 1.

Dim.	Millimeters ^a			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.314	0.357	0.400	0.0124	0.0141	0.0157
A₁	0.127	0.157	0.187	0.0050	0.0062	0.0074
A₂	0.187	0.200	0.213	0.0074	0.0079	0.0084
b	0.165	0.175	0.185	0.0064	0.0068	0.0072
e		0.400			0.0157	
s	0.180	0.200	0.220	0.0070	0.0078	0.0086
D	0.760	0.800	0.840	0.0299	0.0314	0.0330

Notes:

- a. Use millimeters as the primary measurement.

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